Unitized Semiconductor Devices - Page 1 of 1



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Inclosure Material:
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Metal

**Overall Length:** 

1.573 inches

#### **Overall Height:**

0.225 inches

## **Mounting Facility Quantity:**

#### 2

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-3

#### **Component Name And Quantity:**

2 transistor

#### **Mounting Method:**

Unthreaded hole

### Features Provided:

Burn in and gold plated leads

# Semiconductor Material:

Silicon all transistor

### Voltage Rating In Volts Per Characteristic:

-80.0 breakdown voltage, collector-to-base, emitter open all transistor and -80.0 breakdown voltage, collector-to-emitter, with specified

resistance between base and emitter all transistor and 8.0 breakdown voltage, emitter-to-base, collector open all transistor

### **Current Rating Per Characteristic:**

10.00 amperes source cutoff current all transistor

### **Power Rating Per Characteristic:**

50.0 watts small-signal input power, common-collector preset all transistor

### Maximum Operating Tempurature Per Measurement Point:

150.0 degrees celsius case and 175.0 degrees celsius junction

#### **Precious Material And Location:**

Leads gold

**Precious Material:** 

Gold

#### **Terminal Type And Quantity:**

8 pin

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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